

# PATENT ABSTRACTS OF JAPAN

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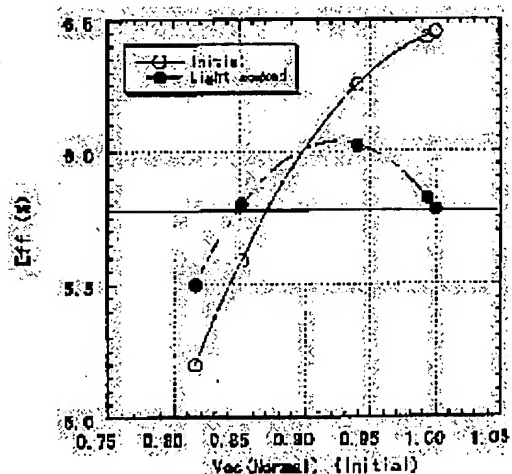
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## (54) NON-MONOCRYSTAL SOLAR BATTERY

### (57)Abstract:

**PROBLEM TO BE SOLVED:** To improve efficiency after irradiation of light in a pin solar battery, using a non-monocrystal thin film.

**SOLUTION:** The film thickness of a p-type semiconductor is set, so that an open voltage before irradiation of light can be set to 0.85–0.99 times as large as the maximum value of the open voltage before irradiation of light. The acceptor impurity concentration of the p-type semiconductor can be set so that the open voltage before the irradiation of light can be set so as to be 0.85–0.99 times as large as the maximum value of the open voltage before the irradiation of light. For the condition of irradiation of light, 10 hours or more is set for 1 SUN, or that (light intensity [SUN]) $\times$ (time [h]) is set at 10 or more.



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